



Reverse Conducting Series

Reverse conducting IGBT with monolithic body diode

IKW30N65WR5

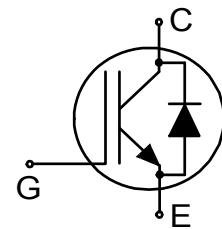
Data sheet

Industrial Power Control

Reverse conducting IGBT with monolithic body diode

Features:

- Powerful monolithic diode optimized for ZCS applications
- TRENCHSTOP™ 5 technology applications offers:
 - high ruggedness, temperature stable behavior
 - very low V_{CEsat} and low E_{off}
 - easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
- Low EMI
- Low electrical parameters depending (dependence) on temperature
- Qualified according to JESD-022 for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>



Applications:

- Welding
- PFC
- ZCS - converters



Key Performance and Package Parameters

Type	V_{CE}	I_c	$V_{CEsat}, T_{vj}=25^\circ\text{C}$	T_{vjmax}	Marking	Package
IKW30N65WR5	650V	30A	1.4V	175°C	K30EWR5	PG-T0247-3

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Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^\circ\text{C}$	V_{CE}	650	V
DC collector current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ $T_C = 117^\circ\text{C}$	I_C	60.0 30.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	90.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^\circ\text{C}$, $t_p = 1\mu\text{s}$	-	90.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_F	24.0 15.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	45.0	A
Gate-emitter voltage	V_{GE}	± 20	V
Power dissipation $T_C = 25^\circ\text{C}$ Power dissipation $T_C = 117^\circ\text{C}$	P_{tot}	185.0 75.0	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		0.81	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		3.40	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		40	K/W

Electrical Characteristic, at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(\text{BR})\text{CES}}$	$V_{\text{GE}} = 0\text{V}, I_{\text{C}} = 0.20\text{mA}$	650	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{\text{GE}} = 15.0\text{V}, I_{\text{C}} = 30.0\text{A}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	-	1.40 1.65	1.80 -	V
Diode forward voltage	V_F	$V_{\text{GE}} = 0\text{V}, I_F = 15.0\text{A}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	-	1.40 1.50	1.90 -	V
Gate-emitter threshold voltage	$V_{\text{GE}(\text{th})}$	$I_{\text{C}} = 0.30\text{mA}, V_{\text{CE}} = V_{\text{GE}}$	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	$V_{\text{CE}} = 650\text{V}, V_{\text{GE}} = 0\text{V}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	-	-	40	μA
Gate-emitter leakage current	I_{GES}	$V_{\text{CE}} = 0\text{V}, V_{\text{GE}} = 20\text{V}$	-	-	100	nA
Transconductance	g_{fs}	$V_{\text{CE}} = 20\text{V}, I_{\text{C}} = 30.0\text{A}$	-	35.0	-	S
Integrated gate resistor	r_G			none		Ω

Electrical Characteristic, at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}		-	3700	-	pF
Output capacitance	C_{oes}	$V_{\text{CE}} = 25\text{V}, V_{\text{GE}} = 0\text{V}, f = 1\text{MHz}$	-	35	-	
Reverse transfer capacitance	C_{res}		-	16	-	
Gate charge	Q_G	$V_{\text{CC}} = 520\text{V}, I_{\text{C}} = 30.0\text{A}, V_{\text{GE}} = 15\text{V}$	-	155.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^\circ\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 25^\circ\text{C}, V_{\text{CC}} = 400\text{V}, I_{\text{C}} = 15.0\text{A}, V_{\text{GE}} = 0.0/15.0\text{V}, R_{G(\text{on})} = 26.0\Omega, R_{G(\text{off})} = 26.0\Omega, L_\sigma = 45\text{nH}, C_\sigma = 32\text{pF}$	-	39	-	ns
Rise time	t_r		-	12	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	367	-	ns
Fall time	t_f		-	9	-	ns
Turn-on energy	E_{on}		-	0.99	-	mJ
Turn-off energy	E_{off}		-	0.33	-	mJ
Total switching energy	E_{ts}	Energy losses include "tail" and diode reverse recovery.	-	1.32	-	mJ

Reverse Conducting Series

Diode Characteristic, at $T_{vj} = 25^\circ\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^\circ\text{C}$, $V_R = 400\text{V}$, $I_F = 15.0\text{A}$, $di_F/dt = 900\text{A}/\mu\text{s}$	-	95	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.25	-	μC
Diode peak reverse recovery current	I_{rrm}		-	22.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-590	-	$\text{A}/\mu\text{s}$

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

IGBT Characteristic, at $T_{vj} = 175^\circ\text{C}$

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 175^\circ\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 15.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 26.0\Omega$, $R_{G(off)} = 26.0\Omega$, $L_\sigma = 45\text{nH}$, $C_\sigma = 32\text{pF}$ L_σ , C_σ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	35	-	ns
Rise time	t_r		-	14	-	ns
Turn-off delay time	$t_{d(off)}$		-	423	-	ns
Fall time	t_f		-	6	-	ns
Turn-on energy	E_{on}		-	1.09	-	mJ
Turn-off energy	E_{off}		-	0.46	-	mJ
Total switching energy	E_{ts}		-	1.55	-	mJ

Diode Characteristic, at $T_{vj} = 175^\circ\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 175^\circ\text{C}$, $V_R = 400\text{V}$, $I_F = 15.0\text{A}$, $di_F/dt = 900\text{A}/\mu\text{s}$	-	121	-	ns
Diode reverse recovery charge	Q_{rr}		-	2.15	-	μC
Diode peak reverse recovery current	I_{rrm}		-	28.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1100	-	$\text{A}/\mu\text{s}$

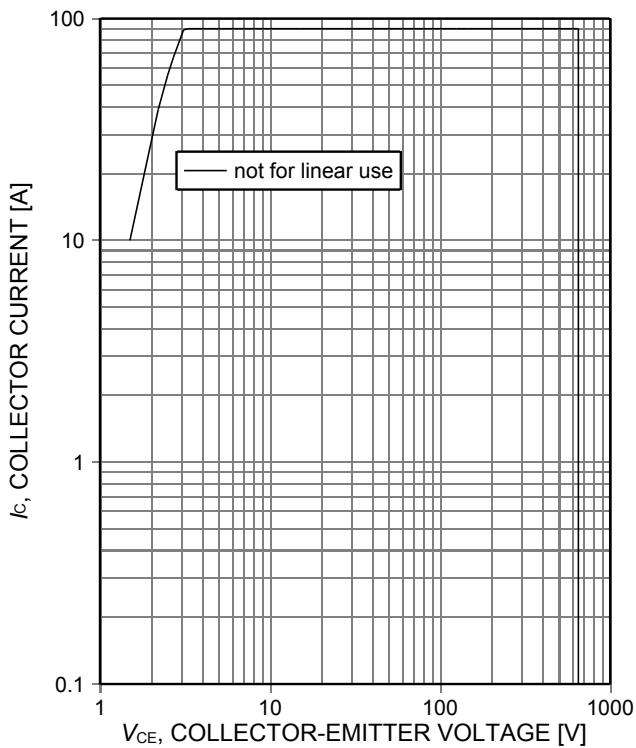


Figure 1. **Forward bias safe operating area**
 $(D=0, T_c=25^\circ\text{C}, T_{vj}\leq 175^\circ\text{C}, V_{GE}=15\text{V}, t_p=1\mu\text{s})$

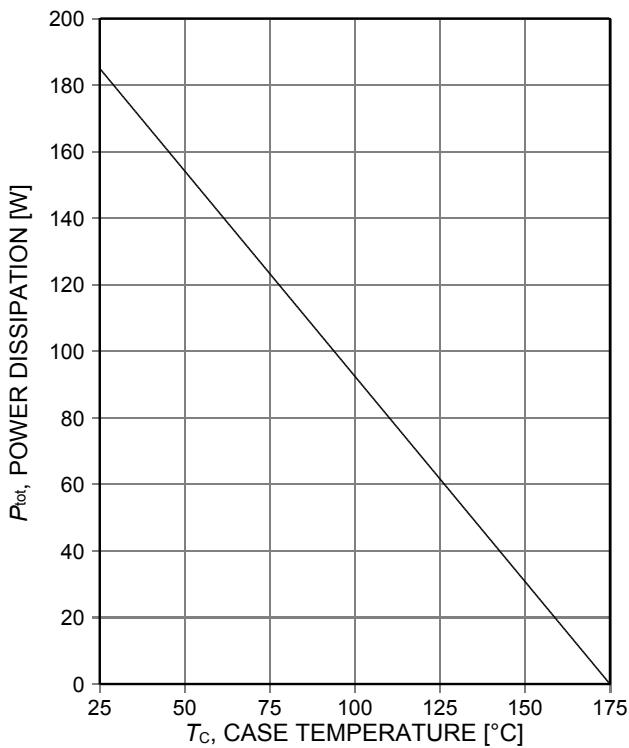


Figure 2. **Power dissipation as a function of case temperature**
 $(T_{vj}\leq 175^\circ\text{C})$

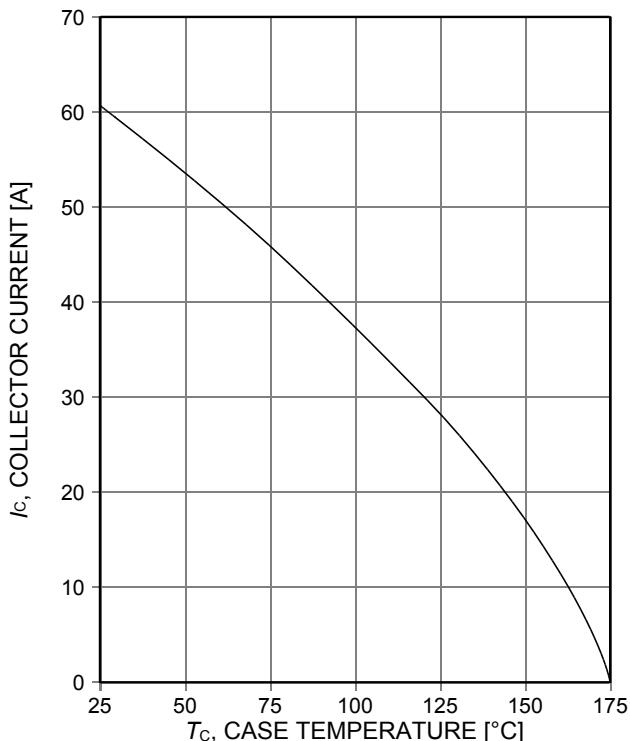


Figure 3. **Collector current as a function of case temperature**
 $(V_{GE}\geq 15\text{V}, T_{vj}\leq 175^\circ\text{C})$

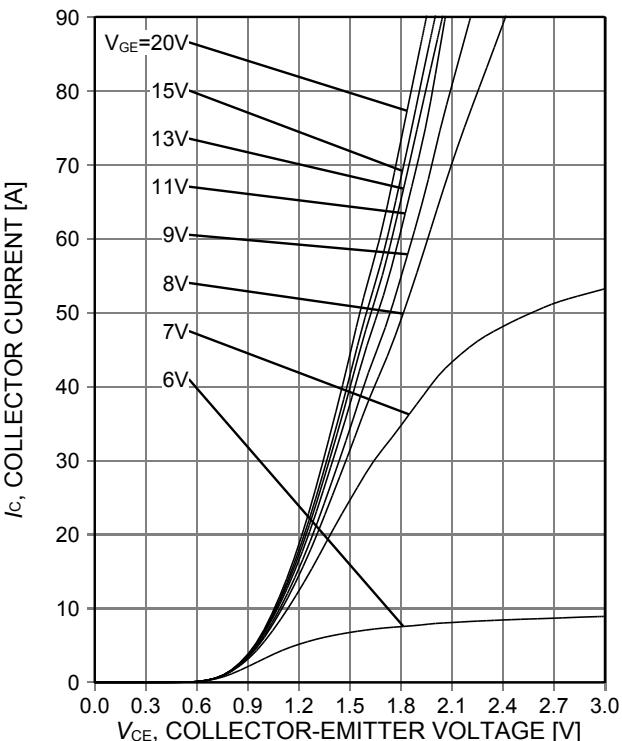


Figure 4. **Typical output characteristic**
 $(T_{vj}=25^\circ\text{C})$

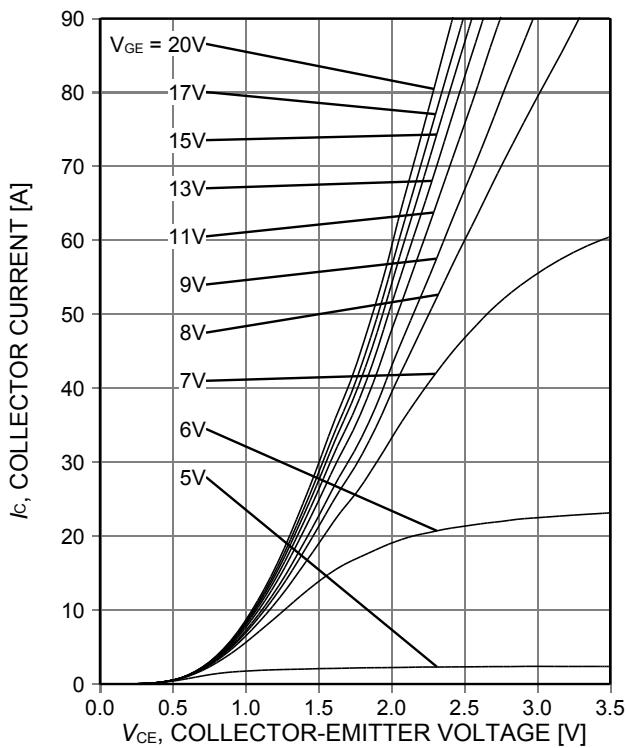


Figure 5. **Typical output characteristic**
($T_{vj}=175^{\circ}\text{C}$)

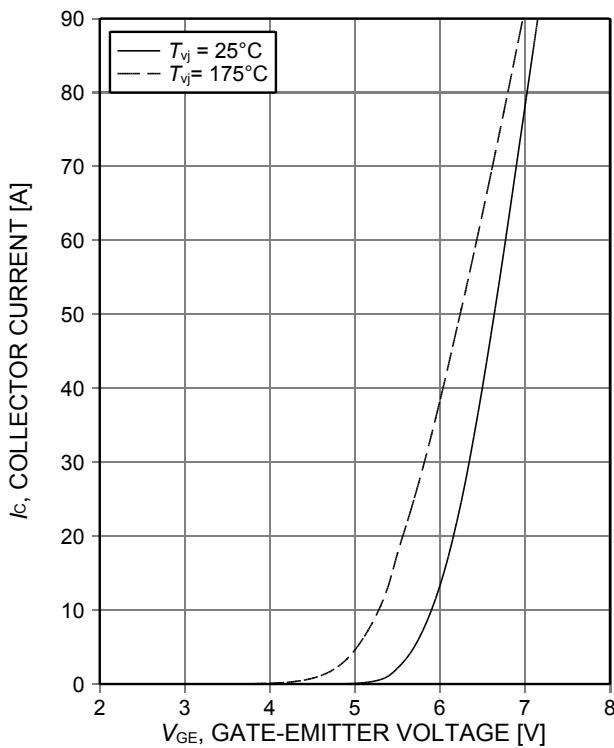


Figure 6. **Typical transfer characteristic**
($V_{CE}=20\text{V}$)

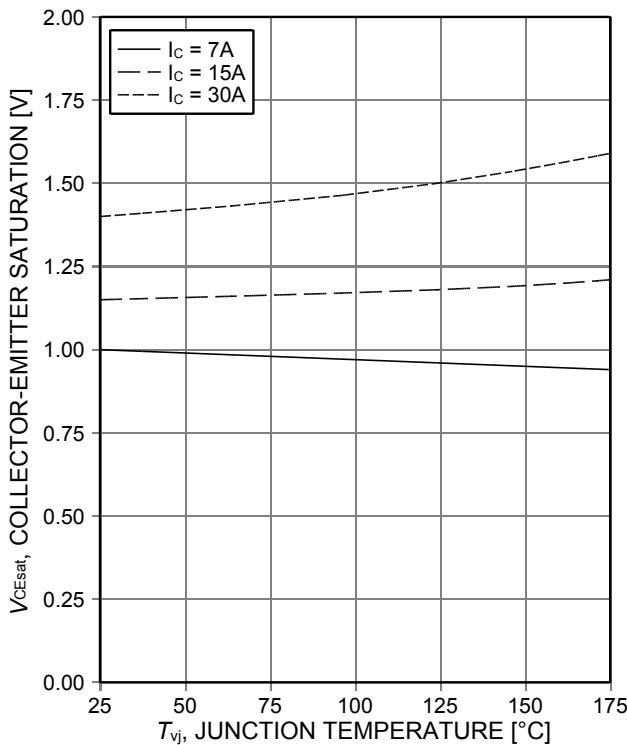


Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15\text{V}$)

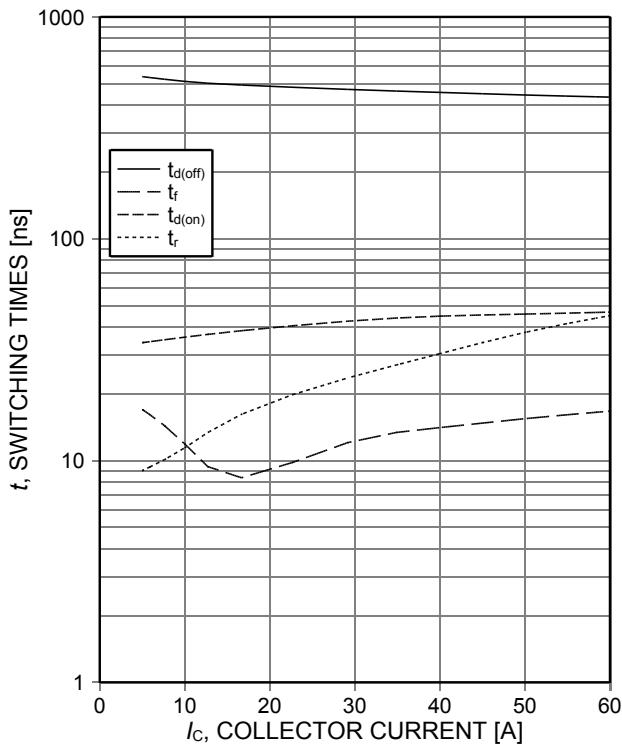


Figure 8. **Typical switching times as a function of collector current**
(inductive load, $T_{vj}=175^{\circ}\text{C}$, $V_{CE}=400\text{V}$,
 $V_{GE}=0/15\text{V}$, $R_{G(\text{on})}=26\Omega$, $R_{G(\text{off})}=26\Omega$, dynamic
test circuit in Figure E)

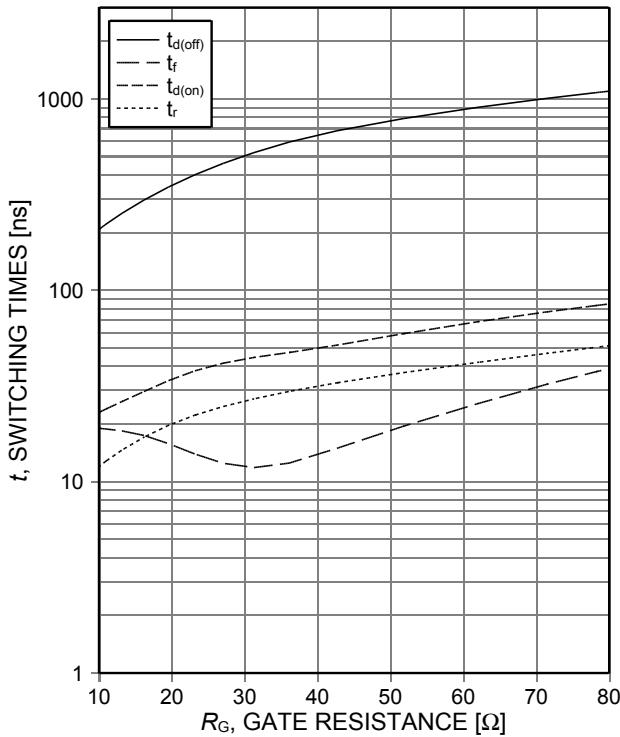


Figure 9. Typical switching times as a function of gate resistance

(inductive load, $T_{vj}=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_c=30\text{A}$, dynamic test circuit in Figure E)

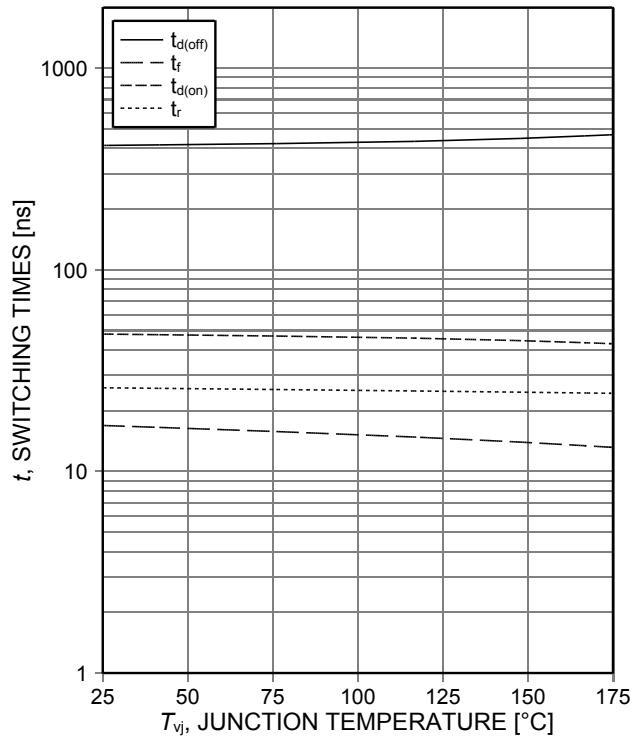


Figure 10. Typical switching times as a function of junction temperature

(inductive load, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_c=30\text{A}$, $R_{G(\text{on})}=26\Omega$, $R_{G(\text{off})}=26\Omega$, dynamic test circuit in Figure E)

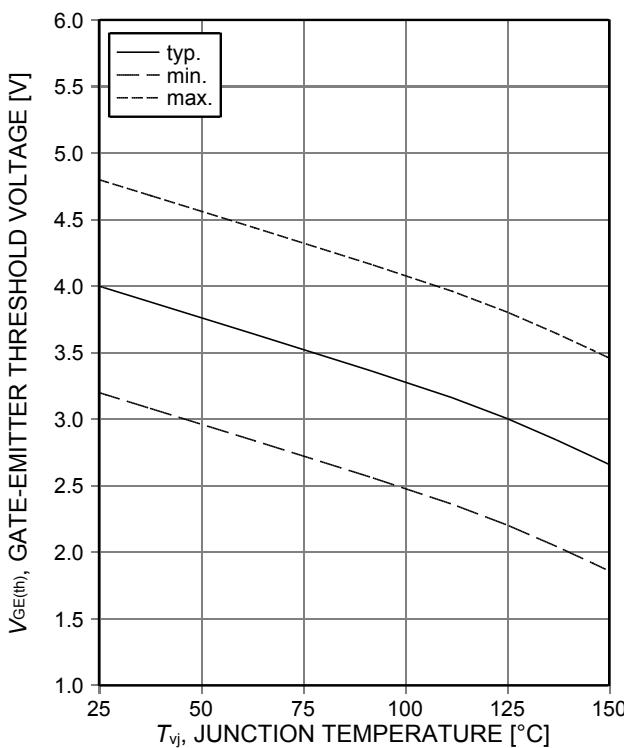


Figure 11. Gate-emitter threshold voltage as a function of junction temperature
($I_c=0.3\text{mA}$)

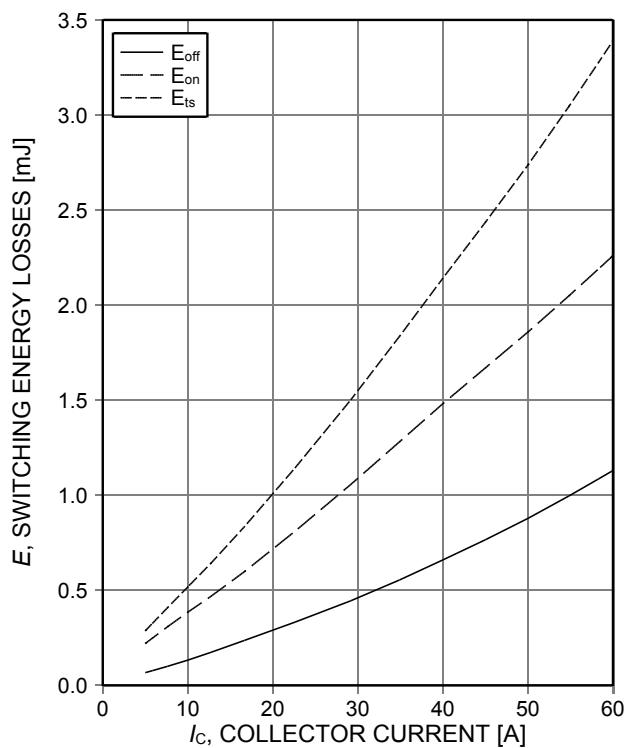


Figure 12. Typical switching energy losses as a function of collector current
(inductive load, $T_{vj}=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $R_{G(\text{on})}=26\Omega$, $R_{G(\text{off})}=26\Omega$, dynamic test circuit in Figure E)

Reverse Conducting Series

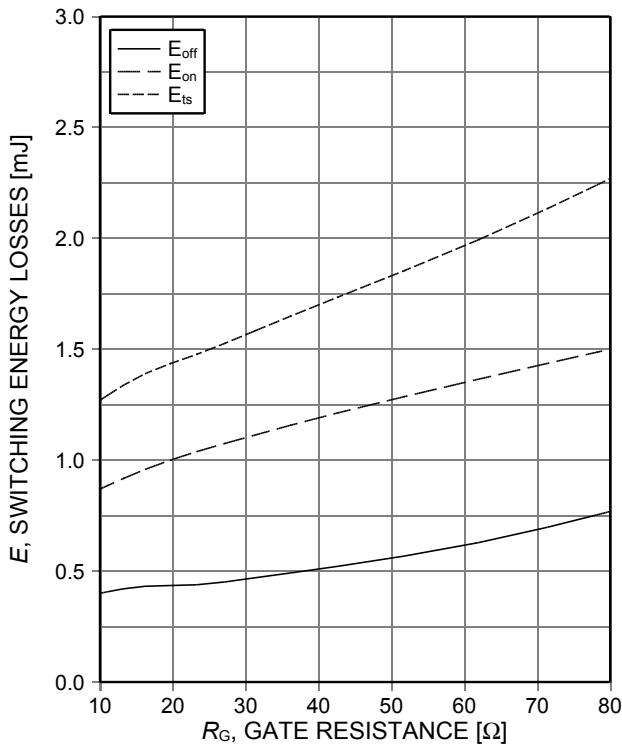


Figure 13. **Typical switching energy losses as a function of gate resistance**
(inductive load, $T_{vj}=175^{\circ}\text{C}$, $V_{CE}=400\text{V}$,
 $V_{GE}=0/15\text{V}$, $I_c=30\text{A}$, dynamic test circuit in
Figure E)

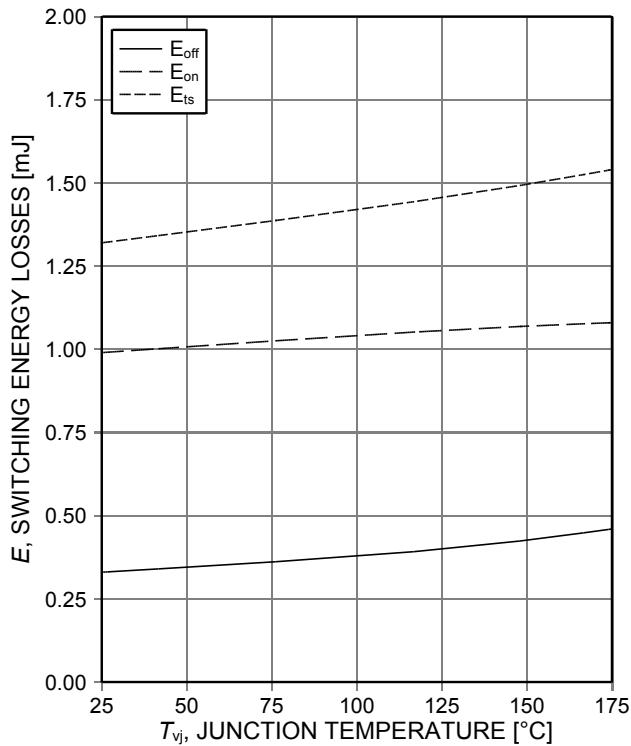


Figure 14. **Typical switching energy losses as a function of junction temperature**
(inductive load, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$,
 $I_c=30\text{A}$, $R_{G(on)}=26\Omega$, $R_{G(off)}=26\Omega$, dynamic
test circuit in Figure E)

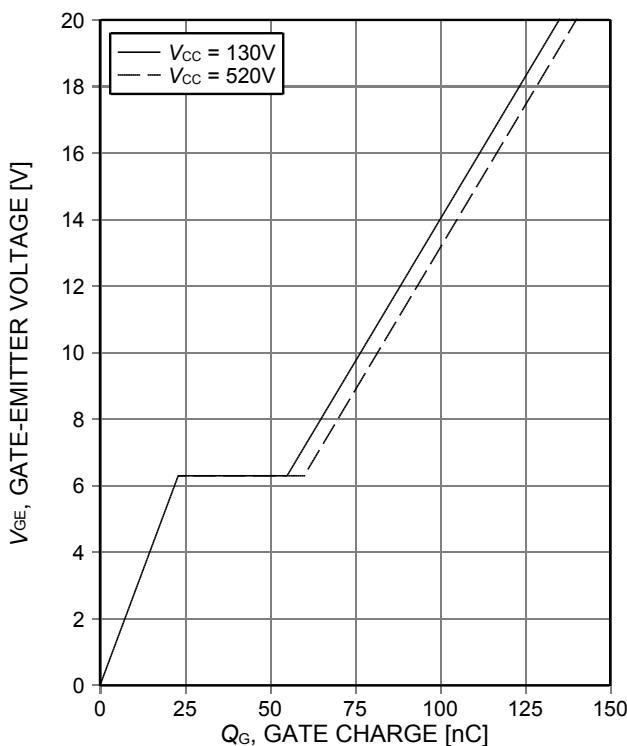


Figure 15. **Typical gate charge**
($I_c=30\text{A}$)

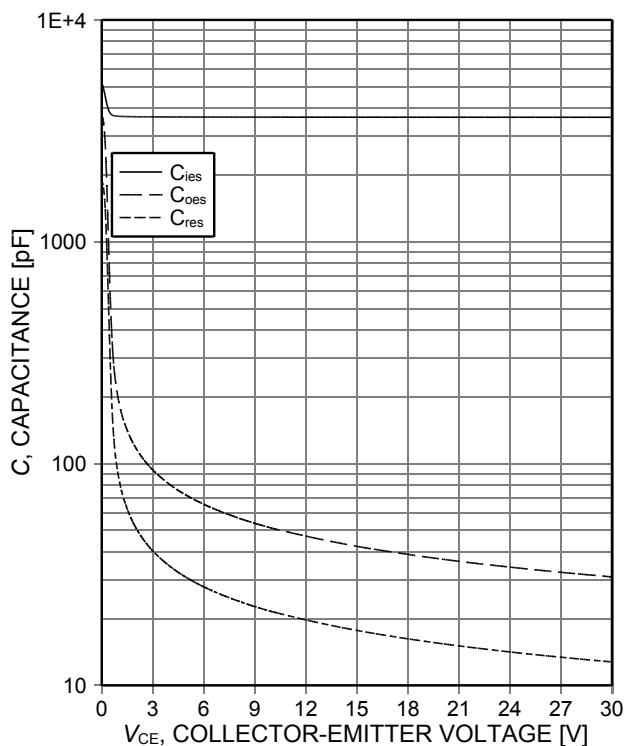


Figure 16. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0\text{V}$, $f=1\text{MHz}$)

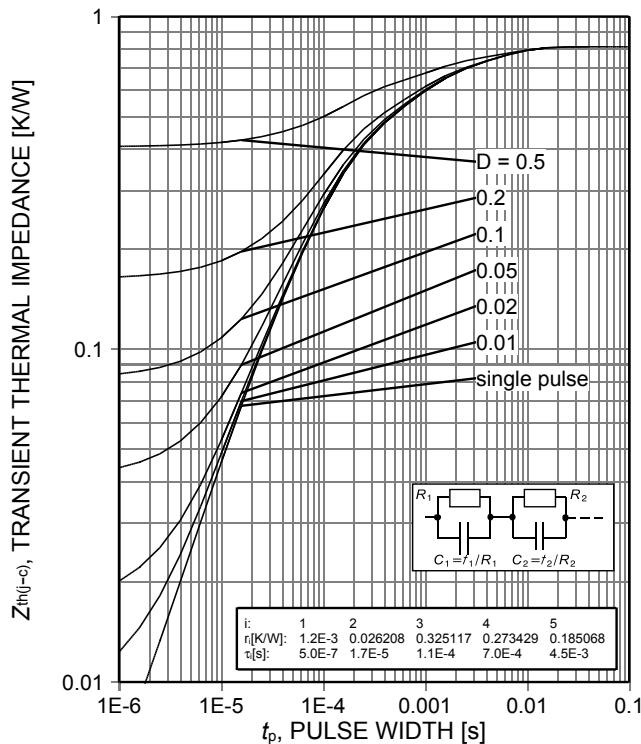


Figure 17. IGBT transient thermal impedance as a function of pulse width ($D=t_p/T$)

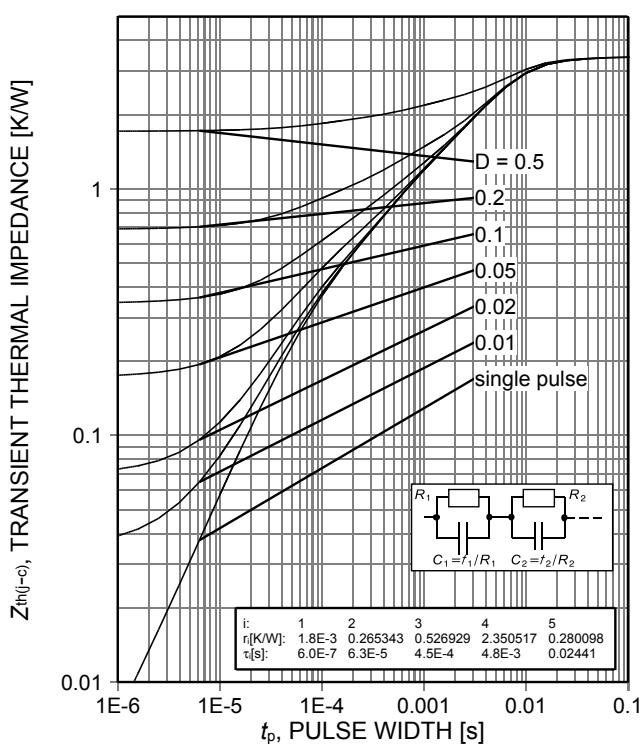


Figure 18. Diode transient thermal impedance as a function of pulse width ($D=t_p/T$)

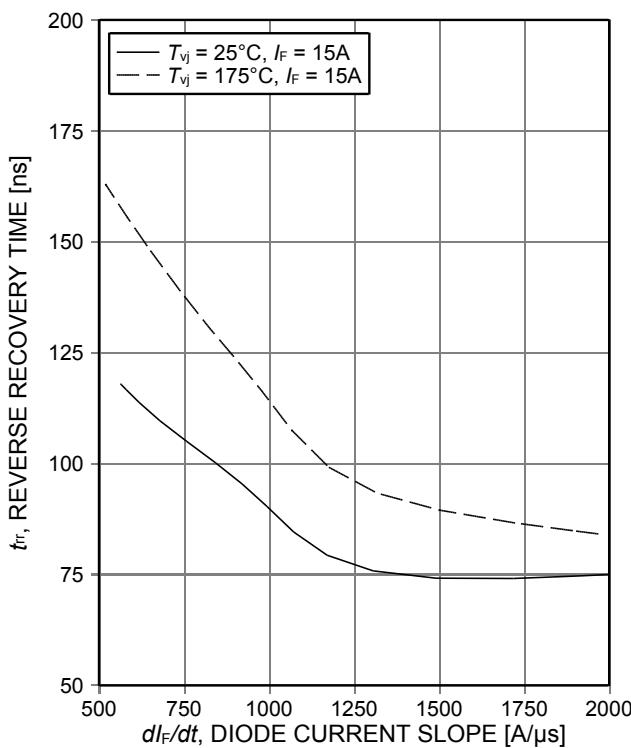


Figure 19. Typical reverse recovery time as a function of diode current slope ($V_R=400\text{V}$)

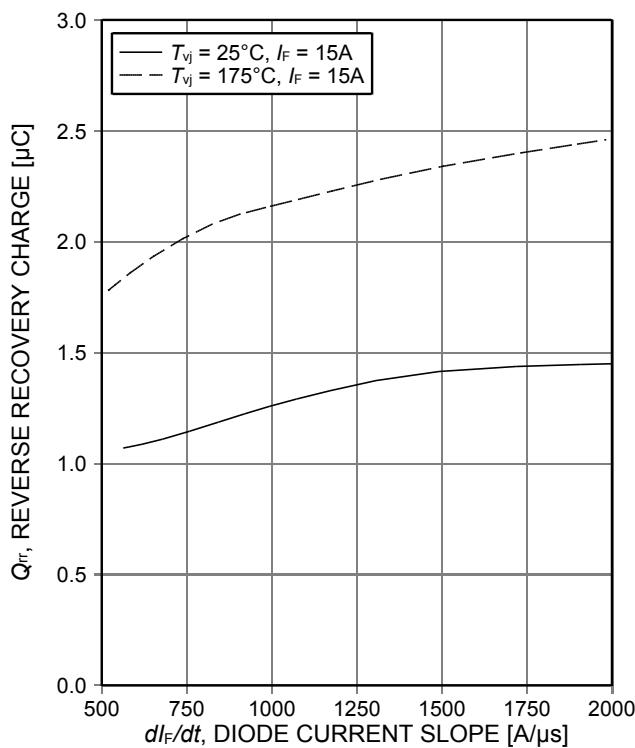


Figure 20. Typical reverse recovery charge as a function of diode current slope ($V_R=400\text{V}$)

Reverse Conducting Series

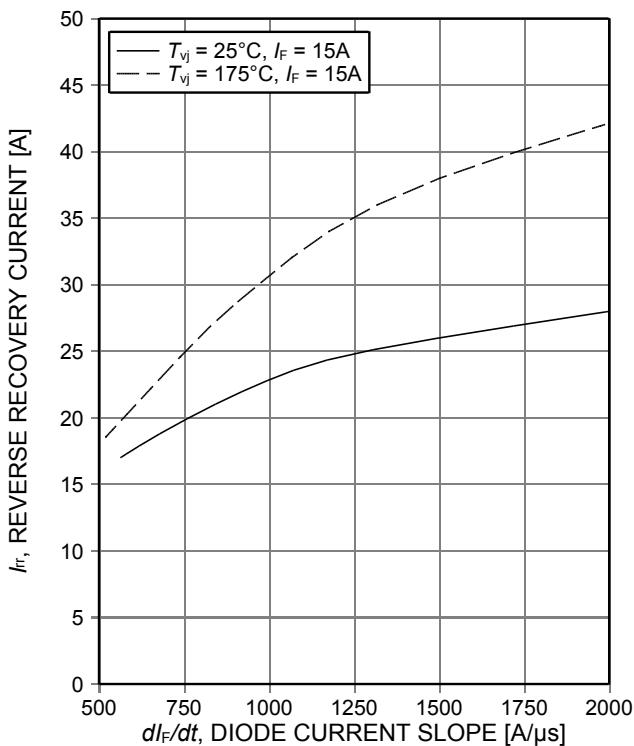


Figure 21. Typical reverse recovery current as a function of diode current slope ($V_R=400V$)

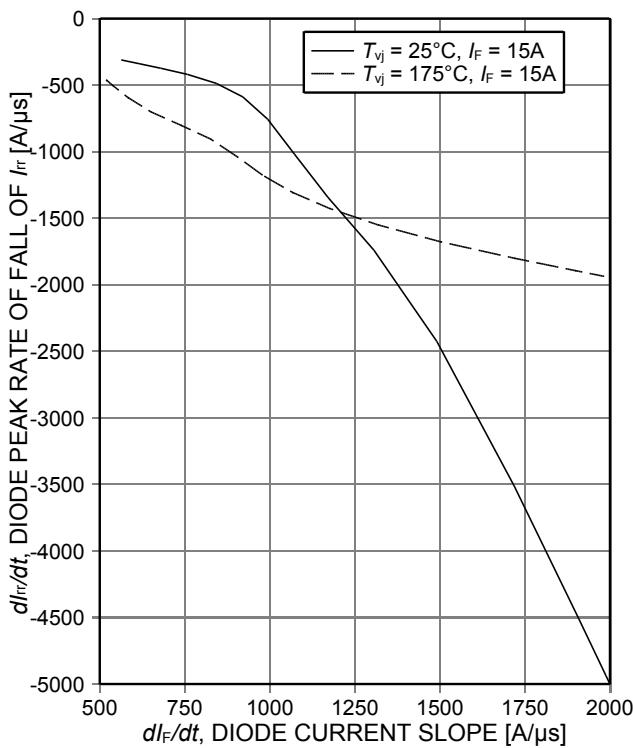


Figure 22. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ($V_R=400V$)

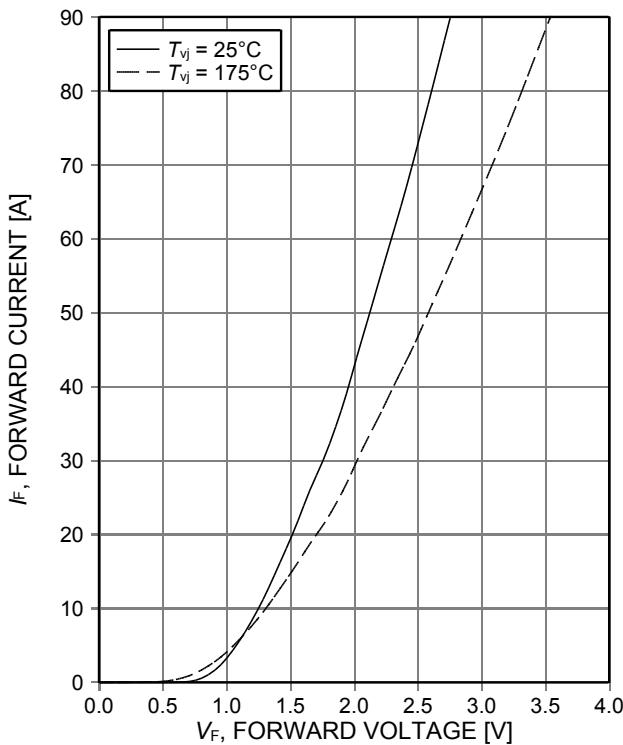


Figure 23. Typical diode forward current as a function of forward voltage

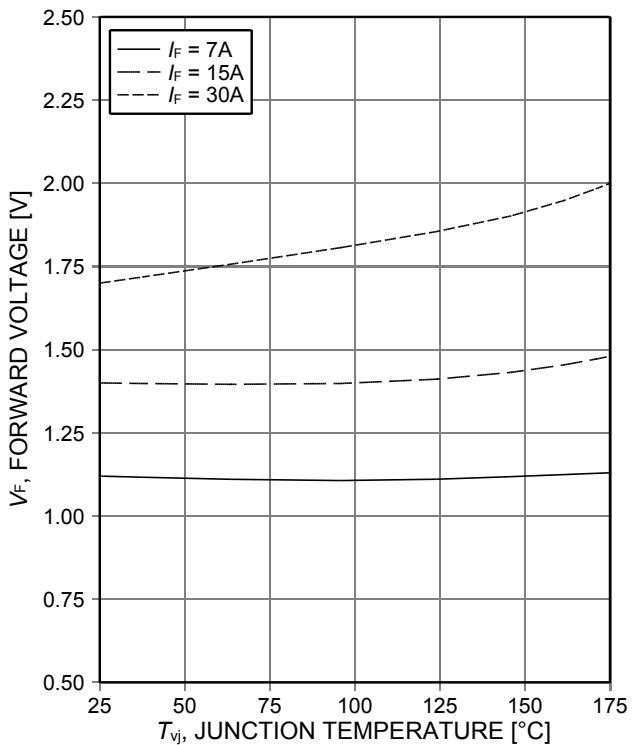
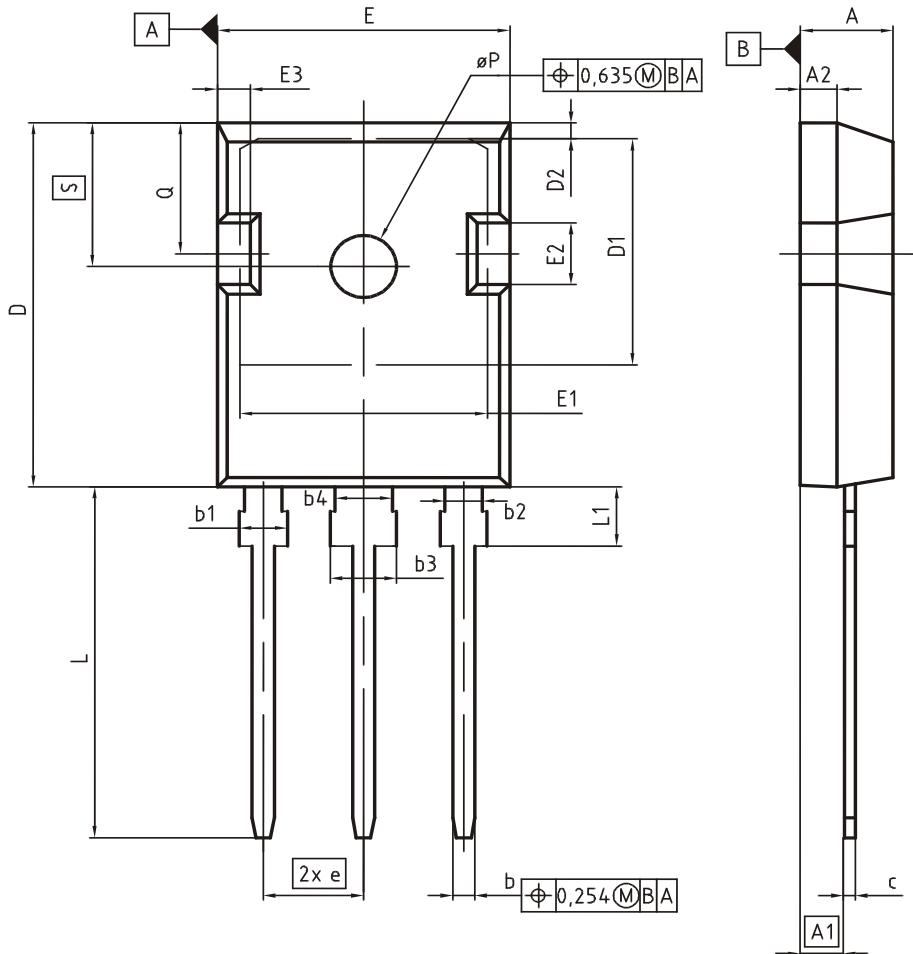


Figure 24. Typical diode forward voltage as a function of junction temperature

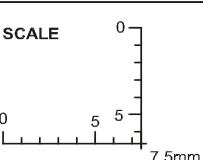
Package Drawing PG-TO247-3



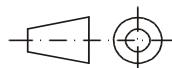
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO.
Z8B00003327

SCALE 0



EUROPEAN PROJECTION



ISSUE DATE
09-07-2010

REVISION
05

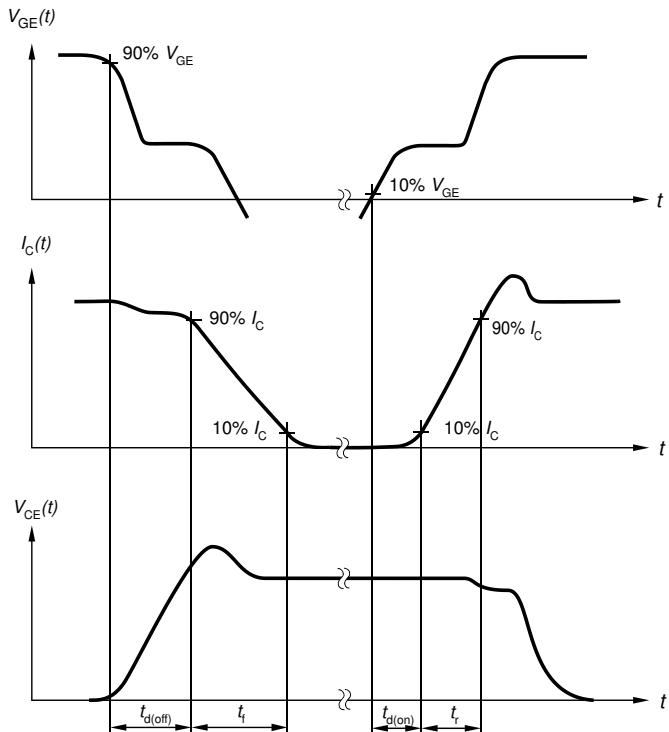
Testing Conditions


Figure A. Definition of switching times

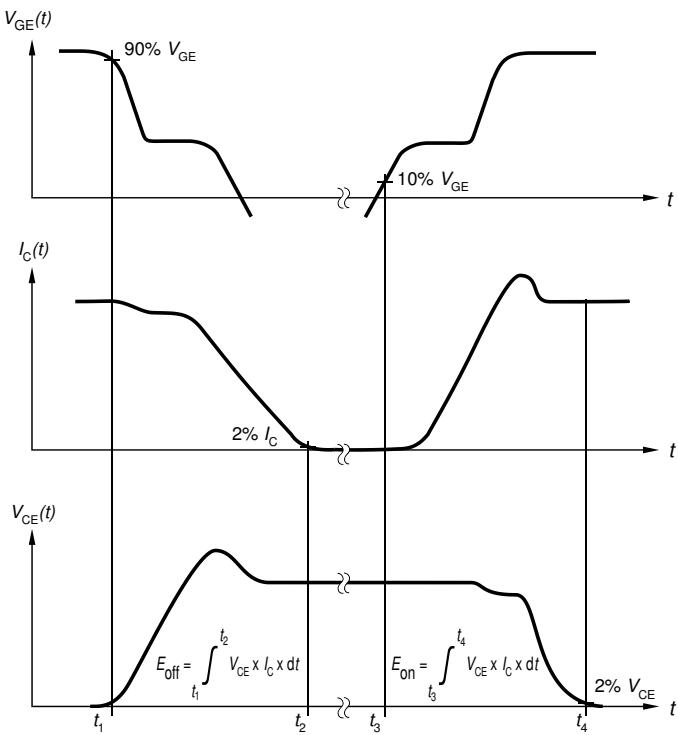


Figure B. Definition of switching losses

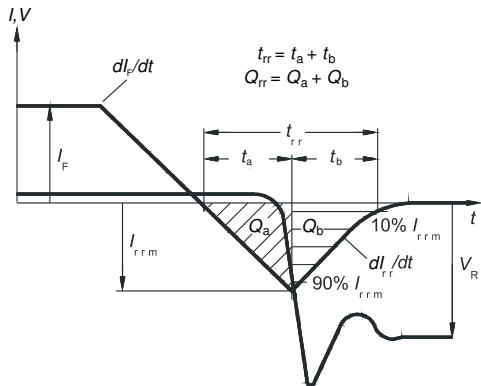


Figure C. Definition of diode switching characteristics

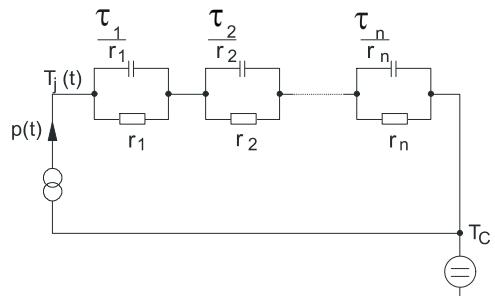
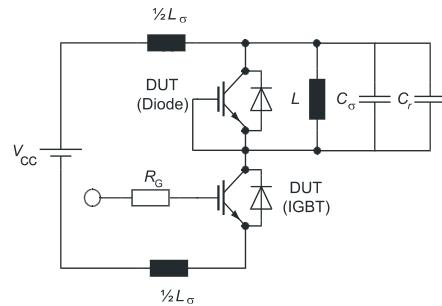


Figure D. Thermal equivalent circuit


Figure E. Dynamic test circuit
Parasitic inductance L_σ ,
parasitic capacitor C_σ ,
relief capacitor C_r ,
(only for ZVT switching)

Revision History

IKW30N65WR5

Revision: 2015-12-10, Rev. 2.1**Previous Revision**

Revision	Date	Subjects (major changes since last revision)
1.1	2015-04-23	Preliminary data sheet
1.2	2015-05-12	Minor change Figure 3
1.3	2015-06-01	Update Figure 14 E(T)
2.1	2015-12-10	Final data sheet

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Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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